2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

Future Normal in Semiconductor

2025-02-14(금), 10:55-12:40

좌장: 추후업데이트 예정

F. Silicon and Group-IV Devices and Integration Technology 분과

[FH2-F] Process-Device Characterization

FH2-F-1 10:55-11:10	Low-Temperature Deuterium Annealing for Improved Immunity against Hot-Carrier Injection in HKMG MOSFETs Ju-Won Yeon, Hyo-Jun Park, Tae-Hyun Kil, Moon-Kwon Lee, Eui-Cheol Yun, Min-Woo Kim, Su-Jin Jeon, Dol Sohn, A-Young Kim, Sang-Min Kang, Da-Eun Bang, and
10.00	Jun-Young Park Chungbuk National University
	Comprehensive Understanding of Polarization Mechanism and Low
FH2-F-2 11:10-11:25	Operating Voltage by Hf0.5Zr0.502 Thickness Scaling on Ge Channel Jai-Youn Jeong ^{1,2} , Kyul Ko ¹ , Changhwan Shin ² , and Jae-Hoon Han ¹ ¹ Center for Opto-electronic Materials and Devices, KIST, ² Device and Circuit Laboratory, Korea University
FH2-F-3 11:25-11:40	Accurate Modeling of NCFET-Based Ring Oscillators Jung Su Kim and Changhwan Shin School of Electrical Engineering, Korea University
	Improvement of Current Drivability through Current Limiter towards
FH2-F-4	Bulk DTMOS with Low-Power High-Performance Operation Versatility
11:40-11:55	Yeji Lim and Seongjae Cho
	Department of Electronic and Electrical Engineering, Ewha Womans University
	Multi-Vt Engineering for Logic Devices Using Rare Earth Oxide-Based
	Dipole-First Approach with Various Interfacial Layer Formation
FH2-F-5	Sang Kuk Han ¹ , Hyun Jin Lim ¹ , Ki Sub Kim ¹ , Hyo Jin Ahn ¹ , Yeh Been Im ¹ , Won Jae
11:55-12:10	Choi ² , Young Seo Na ² , and Changhwan Choi ^{1,2}
	¹ Division of Materials Science and Engineering, Hanyang University, ² Department of
	Semiconductor Engineering, Hanyang University
FH2-F-6 12:10-12:25	Effects of Thermal Annealing Conditions on IGZO-Based MFMIS Ferroelectric TFTs Hyeonjung Park ¹ and Changhwan Shin ²
	¹ Department of Electrical and Computer Engineering, Sungkyunkwan University, ² School of Electrical Engineering, Korea University

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FH2-F-7 12:25-12:40	Atomic Layer Deposition for High-Mobility and Reliable ITZO Thin Film
	Transistors
	Hyeonjin Lee ¹ , Hyeonho Gu ² , Minho Park ² , Yongwoo Lee ² , and Jimin Kwon ^{1,2}
	¹ Graduate School of Semiconductor Materials and Devices Engineering, UNIST,
	² Department of Electrical Engineering, UNIST